

CMS40N03V8-HF

**N-Channel
RoHS Device
Halogen Free**

Features

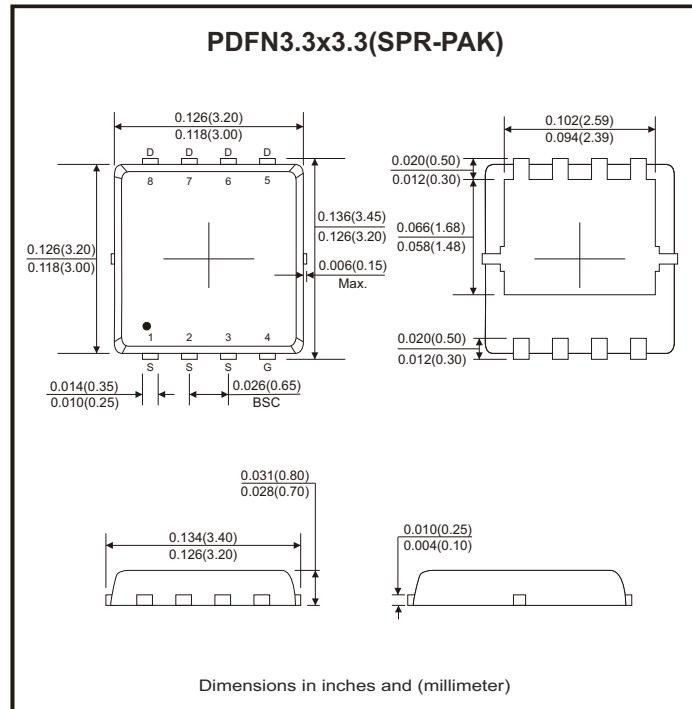
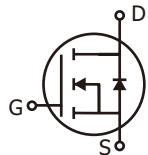
- Low on-resistance.
- Low Miller charge.
- Low input capacitance.
- Green device available.
- 100% EAS and 100% Rg guaranteed.

Mechanical data

- Case: PDFN3.3x3.3/SPR-PAK standard package, molded plastic.

Circuit diagram

- G : Gate
- S : Source
- D : Drain



Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
Drain-source voltage		V _{DS}	30	V
Gate-source voltage		V _{GS}	±20	V
Continuous drain current	I _D @ T _A = 25°C		25	A
	I _D @ T _A = 70°C		20	
Pulsed drain current (Note 1)		I _{DM}	100	A
Continuous drain current (Note 3)	I _D @ T _c = 25°C		40	A
	I _D @ T _c = 70°C		40	
Total power dissipation	P _D @ T _c = 25°C		52	W
	P _D @ T _A = 25°C		3.8	
Single pulse avalanche energy, L=0.1mH		E _{AS}	72	mJ
Single pulse avalanche current, L=0.1mH		I _{AS}	38	A
Operating junction temperature range		T _J	-55 to +150	°C
Storage temperature range		T _{STG}	-55 to +150	°C
Thermal resistance junction-ambient (Note 2)	t ≤ 10s	R _{θJA}	33	°C/W
Thermal resistance junction-case (Note 2)	Steady state	R _{θJC}	2.4	°C/W

Electrical Characteristics (at $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	30			V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	1.15		2.2	
Forward transconductance (Note 1)	g_{fs}	$V_{\text{DS}} = 15\text{V}, I_{\text{D}} = 19\text{A}$		82		S
Gate-source leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Drain-source leakage current	I_{DSS}	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Static drain-source on-resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 19\text{A}$		3.4	4.8	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 16\text{A}$		4.7	5.8	
Total gate charge	Q_{g}	$I_{\text{D}} = 19\text{A}, V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 4.5\text{V}$		12		nC
Gate-source charge	Q_{gs}			6		
Gate-drain ("miller") charge	Q_{gd}			5		
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 4.5\text{V}$ $I_{\text{D}} = 10\text{A}, R_{\text{G}} = 1\Omega, R_{\text{L}} = 1.5\Omega$		24		nS
Rise time	t_{r}			21		
Turn-off delay time	$t_{\text{d(off)}}$			25		
Fall time	t_{f}			17		
Input capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 15\text{V}, f = 1\text{MHz}$		1750		pF
Output capacitance	C_{oss}			360		
Reverse transfer capacitance	C_{rss}			150		
Gate resistance	R_{g}	$f = 1\text{MHz}$		3.2		Ω
Source-drain diode						
Max. body-diode continuous current	I_{s}				40	A
Diode forward voltage	V_{SD}	$I_{\text{s}} = 10\text{A}, V_{\text{GS}} = 0\text{V}$		0.8	1.2	V
Reverse recovery time	t_{rr}	$I_{\text{F}} = 10\text{A}, T_J = 25^\circ\text{C}$ $dI/dt = 100\text{A}/\mu\text{s}$		25		nS
Reverse recovery charge	Q_{rr}			17		
Guaranteed avalanche characteristics						
Single pulse avalanche energy (Note 4)	EAS	$V_{\text{DD}} = 20\text{V}, L = 0.1\text{mH}, I_{\text{AS}} = 31\text{A}$	48			mJ

Notes: 1. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

2. R_{GA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{GC} is guaranteed by design while R_{CA} is determined by the user's board design.

R_{GA} shown below for single device operation on FR-4 in still air.

3. The maximum current rating is limited by package.

4. The min. value is 100% EAS tested guarantee.

Rating and Characteristic Curves (CMS40N03V8-HF)

Fig.1 - Typical Output Characteristics

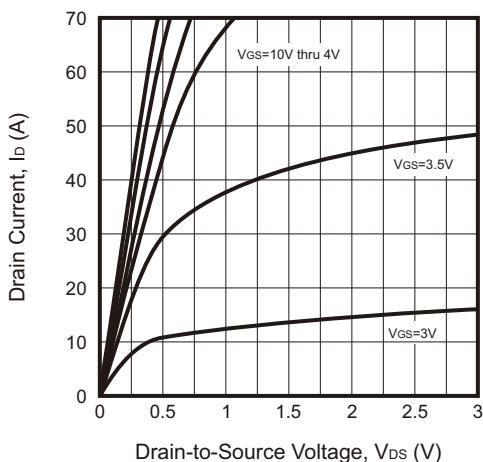


Fig.2 - On-Resistance vs. G-S Voltage

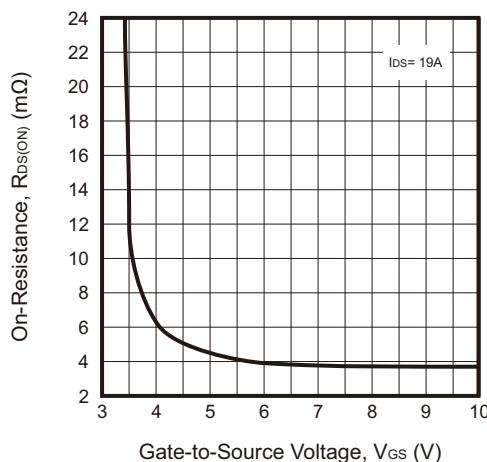


Fig.3 - On-Resistance vs. Drain Current

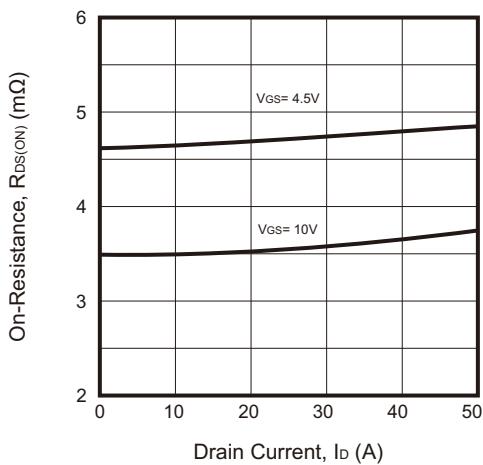


Fig.4 - Normalized $R_{DS(ON)}$ vs. T_J

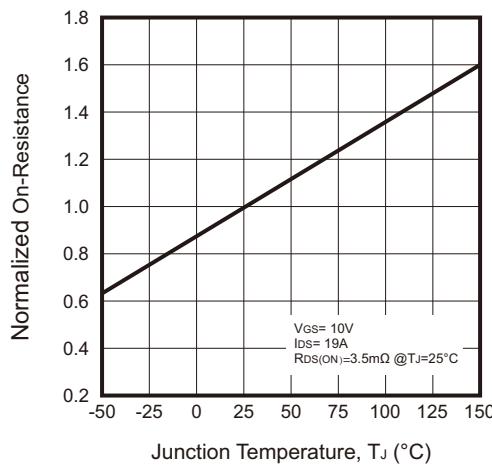


Fig.5 - Normalized $V_{GS(th)}$ vs. T_J

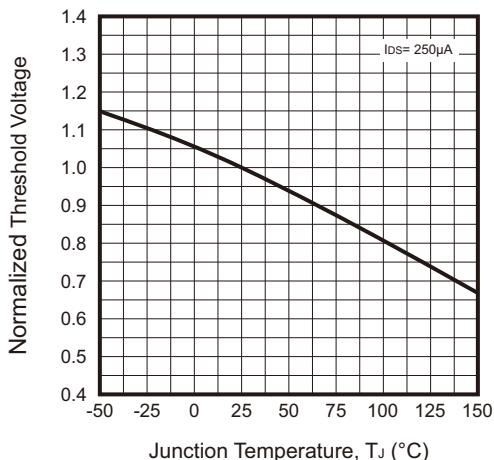
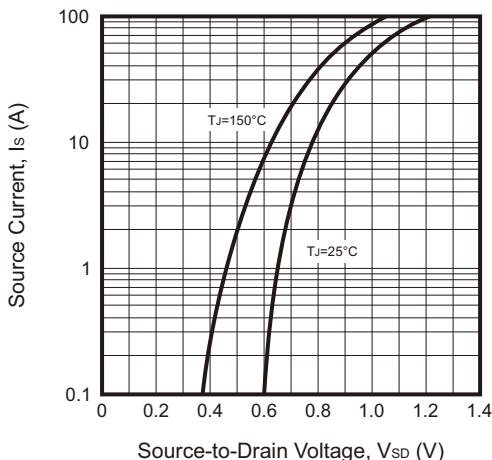


Fig.6 - Forward Characteristics of Reverse



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REV:A

Rating and Characteristic Curves (CMS40N03V8-HF)

Fig.7 - Gate Charge Characteristics

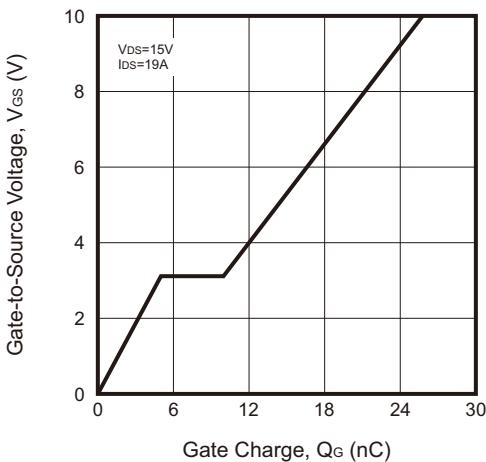


Fig.8 - Capacitance Characteristics

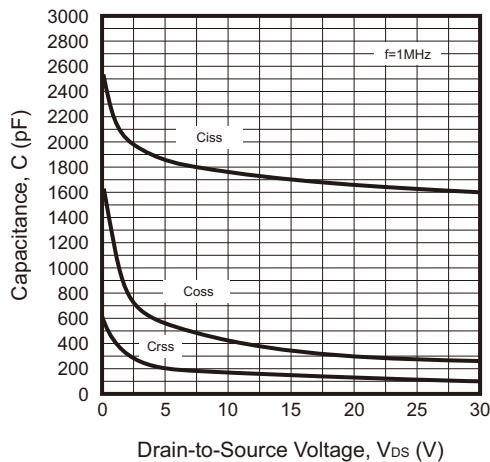


Fig.9 - Safe Operating Area

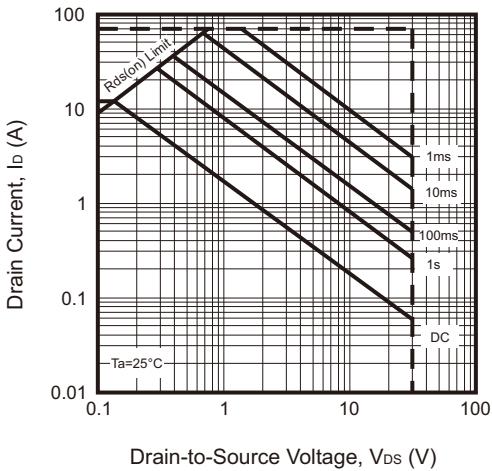


Fig.10 - Power Dissipation

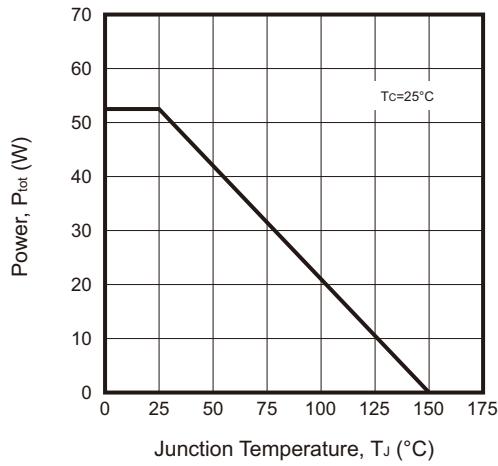
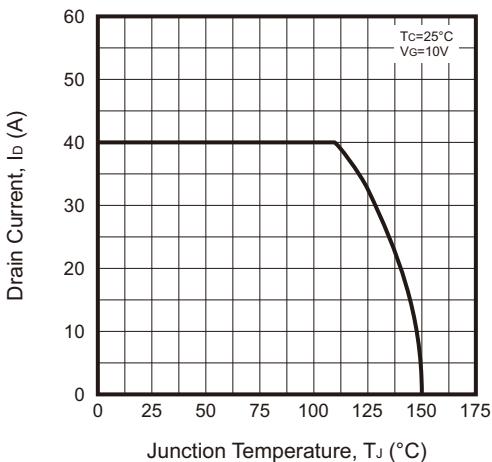


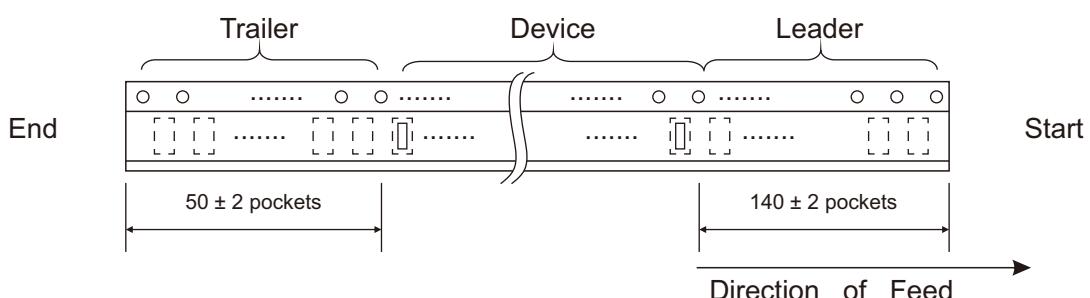
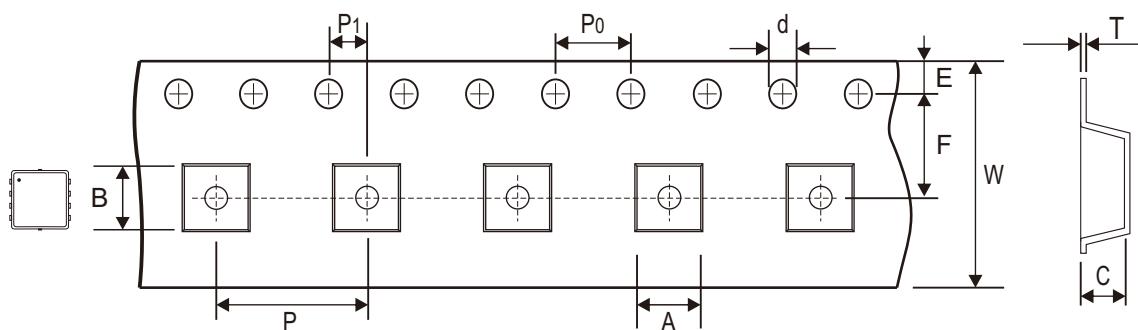
Fig.11 - Drain Current vs. T_J



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REV:A

Reel Taping Specification



SPR-PAK	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	3.55 ± 0.10	3.55 ± 0.10	$1.10 + 0.10$ - 0.05	$1.50 + 0.10$ - 0.00	330.00 ± 1.00	$178.00 + 0.00$ - 2.00	13.00 min.
	(inch)	0.140 ± 0.004	0.140 ± 0.004	$0.043 + 0.004$ - 0.002	$0.059 + 0.004$ - 0.000	12.992 ± 0.039	$7.008 + 0.000$ - 0.079	0.512 min.

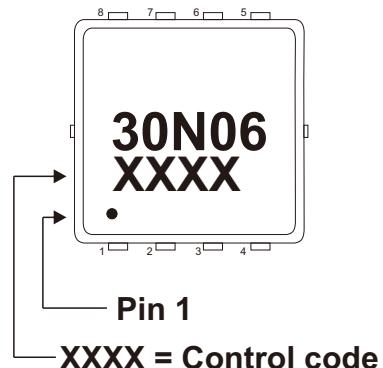
SPR-PAK	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	5.50 ± 0.05	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	0.30 ± 0.05	$12.00 + 0.30$ - 0.10	18.40 ref.
	(inch)	0.069 ± 0.004	0.217 ± 0.002	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.012 ± 0.002	$0.472 + 0.012$ - 0.004	0.724 ref.

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REV:A

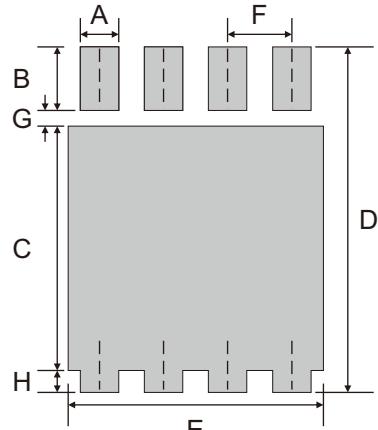
Marking Code

Part Number	Marking Code
CMS40N03V8-HF	30N06



Suggested PAD Layout

SIZE	SPR-PAK (PDFN3.3x3.3)	
	(mm)	(inch)
A	0.40	0.016
B	0.60	0.024
C	2.35	0.093
D	3.55	0.140
E	2.80	0.110
F	0.65	0.026
G	0.35	0.014
H	0.25	0.010



Note: 1. The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SPR-PAK (PDFN3.3x3.3)	3000	13